Rajan Sir's BERIT-HOME Learning Centre

IIT-JEE/NEET/MHTCET/FOUNDATION

Centres

Chinchwad

Thergaon

7770006629

Subject: Chemistry MHT-CET-QUESTION PAPER **Total Marks: 50**

Time: 1 Hr. Class: XII **Topic: 1. Solid State**

- 1) Silicon is
 - a) semiconductor b) insulator
 - c) conductor
- d) none of these
- 2) A metallic element has a cubic lattice. Each edge of the unit cell is 2 A. The density of the metal is 2.5 g cm⁻³. The unit cells in 200 g of metal are
 - a) 1×10^{24}
- b) 1×10^{20}
- c) 1×10^{22}
- d) 1×10^{25}
- A metal has a fcc lattice. The edge length 3) of the unit cell is 404 pm. The density of the metal is 2.72gcm⁻³. The molar mass of the metal is (N, Avogadro's constant = $6.02 \times 10^{23} \text{ mol}^{-1}$
 - a) 40 g mol⁻¹
- b) 30 g mol⁻¹
- c) 27 g mol⁻¹
- d) 20 g mol⁻¹
- Select a ferromagnetic material from the 4) followings.
 - a) Dioxygen
 - b) Chromium (IV) oxide
 - c) Benzene
 - d) Dihydrogen monoxide
- In face centred cubic unit cell, what is the 5) volume occupied?

 - a) $\frac{4}{3}\pi r^3$ b) $\frac{8}{3}\pi r^3$
 - c) $\frac{16}{3}\pi r^3$
- d) none of these
- Which among the following solids is a nonpolar solid?
 - a) Hydrogen chloride
 - b) Sulphur dioxide
 - c) Water
- d) Carbon dioxide
- In which among the following solids, 7)

- Schottky defect is NOT observed?
- a) ZnS
- b) NaCl
- c) KCl
- d) CsCl
- Which among the following solids shows Frenkel defect?
 - a) NaCl
- b) CsCl
- c) AgCl
- d) KCl
- 9) Which among the following pairs of compounds is NOT isomorphous?
 - a) NaNO, and CaCO,
 - b) NaF and MgO
 - c) K₂SO₄ and K₂SeO₄
 - d) NaCl and KCl
- 10) The percentage of unoccupied volume in simple cubic cell is
 - a) 52.40%
- b) 32.00%
- c) 68.04%
- d) 47.60%
- 11) Which among the following ferromagnetic in nature?
 - a) Oxygen
- b) Benzene
- c) Water
- d) Iron
- 12) Which among the following is NOT an amorphous solid?
 - a) Tar
- b) Camphor
- c) Butter
- d) Rubber
- 13) Which of the following is ferromagnetic in nature?
 - a) Gadolinium
- b) Oxygen
- c) Water
- d) Benzene
- 14) Which among the following elements when added to silicon forms P - type semiconductor?

	a) Sb	b) Bi		ber of valence elec	ctrons	
	c) As	d) B		a) 3	b) 5	
15)	Which among	the following crystal		c) 1	d) 2	
,	_	lge length of unit cell is	24)	What is known as brown coal?		
		e radius of one atom?		a) peat	b) lignite	
	a) End — centred		25	c) bituminous	d) anthracite	
	b) Simple cubic	ormomomore	25)	NaCl shows	h) Sahattlar dafaat	
	, 1	_1. : _		, , , , , , , , , , , , , , , , , , ,	b) Schottky defect	
	,	c) Body centred cubic		(c) Interstitial defects (d) Line defect An example of a substitual impurity		
	d) Face centred cubic		26)	defect is		
16)	If 'a' is edge length of a simple cubic unit			a) KCI	b) ZnS	
		cell, then atomic radius is given as		c) Brass	d) CgC	
	a) 0.1 a	b) 0.5 a	27)	Where is the Nati	onal Institute of Rural	
	c) a	d) 1.5 a		Development loc	ated?	
17)	Copper crystalliz	zes as face centred cubic		a) Shimla	b) Hyderabad	
	lattice, with edge	e length of unit cell 361		c) Patna	d) New Delhi	
	pm. Calculate the radius of copper atom.		28)	The size of tetrahedral voids formed by spheres as compared to octahedral voids		
	a) 108.6 pm	b) 127.6 pm		spneres as compa formed is	rea to octanearal voias	
	c) 157.6 pm	d) 181.6 pm		a) Equal	b) Smaller	
18)	An element crys	tallises in bcc structure.		c) Greater	d) Indefinite	
	The number of unit cells of an element in 4 g of it is (Given- At mass = 40)		29)	In the BCC lattice structure, the radius of		
			,	the sphere is 75 pm. The edge length of the		
	a) $2 \times 0.1 \text{ N}$	b) 0.2 × N	0.	unit cell is	0 0	
	c) $0.1 \times N/2$	d) 0.1 N	A	a) 32.475 Pm	b) 212.1 Pm	
19)	,		80	c) 37.5 Pm	d) 173.2 Pm	
1),	Aluminium crystallizes in face centred cubic structure, having atomic radius 125 pm. The edge length of the unit cell of		30)	Due to the Frenkel defect, the density of		
				the ionic solid	1) 5	
	aluminium is	ngth of the unit cen of	Ó.	a) Increases	b) Decreases	
	a) 250.0 pm	b) 353.5 pm	20	c) Remains constad) Fluctuates	ını	
	, <u>.</u>	The second secon	31)	/	ons moved from their	
20)	c) 465.0 pm	d) 253.5 pm			e interstitial sites in a	
20)	Which among the following is NOT paramagnetic in nature?			crystalline solid, it is		
				a) Interstitial defea		
	a) Benzene	b) Fe ³⁺		b) Frenkel defect		
	c) Cu ²⁺	d) Oxygen		c) Schottky defect		
21)		The mass fcc type unit cell of copper is		d) Line defects		
	419×10^{24} g What is the mass of one atom		32)	,		
	of copper?			ent types of unit of		
	a) 1.047×10^{-21}	b) 2.09×10^{21}		a) FCC > BCC < 5b) FCC > BCC > 5	-	
	c) 1.048×10^{-22}	d) $4.19 \times 10^{-24} \text{ g atom}^{-1}$		*	-	
22)	tor, impurity atoms are added to have a number of valence electrons			 c) FCC < BCC > Simple cubic d) BCC < FCC < Simple cubic 33) In a closest-packed lattice, the number of tetrahedral voids formed will be 		
			33)			
			,			
	a) 3 b)5 c)	1 d) 2			umber of spheres in the	
23)	In the formation of an n-type semiconductor, impurity atoms are added to have a num-			lattice.		
				b) Half of that of a 1	number of spheres.	
					1	

c) Double that of a number of spheres. d) One-fourth of that of a number of spheres. If 'R' is the radius of the spheres in the CCP arrangement and 'Y' is the radius of the octahedral voids, then a) r = 0.414 R b) r = 0.224 R c) R = 0.414 r d) R = 0.224 R d) The condition of Cl ⁻ ions is a) fec b) bcc d) None of these 36) If the coordination number of an element in its crystal lattice is 8, then packing is: a) fc b) hcp c) bce d) none of the above 37) The total number of identical spheres required in cubic close packing arrangement of a unit cell is a) 6 b) 8 c) 12 d) 14 38) Which of the following types of semiconductor are used as transistors? a) n-p-n type b) p-n-p type c) p-n type d) Both(a) and (b) 39) To get a n-type semiconductor, the impurity to be added to silicon should have which of the following number of valence electrons? a) 1 b) 2 c) 3 d) 5 40) A semiconductor of Si can be made p-type by adding a) trivalent impurity d) divalent impurity c) pentavalent impurity d) divalent impurity d) divalent impurity d) divalent impurity e) pertavalent impurity d) divalent impurity d) divalent impurity d) divalent impurity e) pertavalent				ı			
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34) If 'R' is the radius of the spheres in the CCP arrangement and 'Y' is the radius of the octahedral voids, then a) r = 0.414 R b) r = 0.224 R c) R = 0.414 R d) R = 0.224 r 35) In crystal structure of sodium chloride, the arrangement of CF ions is a) fec b) bec c) Both fec and bec d) None of these 36) If the coordination number of an element in its crystal lattice is 8, then packing is: a) fe b) hep c) bec d) none of the above 37) The total number of identical spheres required in cubic close packing arrangement of a unit cell is a) 6 b) 8 c) 12 d) 14 38) Which of the following types of semiconductor are used as transistors? a) n-p-n type b) p-n-p type c) p-n type d) Both(a) and (b) 37) To get a n-type semiconductor, the impurity to be added to silicon should have which of the following number of valence clectrons? a) 1 b) 2 c) 3 d) 5 40) A semiconductor of Si can be made p-type by adding a) trivalent impurity b) tetravalent impurity c) eptavalent impurity d) divalent impurity e) b) tetravalent impurity d) divalent impurity d) divalent impurity e) parangenetic c) parangenetic c) parangenetic c) parangenetic c) parangenetic c) parangenetic c) parangenetic ci n anture? a) MnO₂ b) TiO₂ c) c) CrO₂ 43) Which of the following metal oxides is antiferromagnetic in nature? a) MnO₂ b) TiO₂ c) c) CrO₂ 43) Which of the following is not an antiferromagnetic compound?		· ·			c) Mn ₂ O ₃	d) CrO ₂	
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